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Application Number	
Filing Date	Feb. 18, 2004
First Named Inventor	Wu, Koucheng
Art Unit	2826
Examiner Name	
Attorney Docket Number	KWU003

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of

Attorney Docket Number **KWU003**

U. S. PATENT DOCUMENTS

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Wu, Koucheng

KWU003

NON PATENT LITERATURE DOCUMENTS

Examiner Initials*	Cite No. ¹	Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date, page(s), volume-issue number(s), publisher, city and/or country where published.	T ²
	1	M. P. LEPSELTTER and S. M. SZE, "SB-IGFET: An Insulated-Gate Field-Effect Transistor Using Schottky	
		Barrier Contacts for Source and Drain", Proc. IEEE, pp. 1400-1402, Aug. 1968.	
	2	J. R. TUCKER, C. WANG, and P. S. CARNEY, "Silicon Field-Effect Transistor Based on Quantum	
		Tunneling", Appl. Phys. Lett, vol. 65, no. 5, pp. 618-620, Aug. 1994.	
	3	B. WINSTEAD and U. RAVAIOLI, "Simulation of Schottky Barrier MOSFET's with a Coupled Quantum	
		Injection/Monte Carlo Technique", IEEE Trans. Electron Devices, vol. 47, no. 6, pp. 1241-1246,	
		Jun. 2000.	
	4	J. KEDZIERSKI, P. XUAN, E. H. ANDERSON, J. BOKOR, T.-J. KING, and C. HU, "Complementary Silicide	
		Source/Drain Thin-Body MOSFETs for the 20nm Gate Length Regime", IEDM Tech. Digest, pp. 57-60, 2000	

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	5	J. D. PLUMMER and P. B. GRIFFIN, "Material and Process Limits in Silicon VLSI Technology",	
		Proc. IEEE, vol. 89, no. 3, pp. 240-258, 2001.	
	6	D. J. FRANK, R. H. DENNARD, E. NOWAK, P. M. SOLOMON, Y. TAUR, and H.-S. P. WONG, "Device Scaling	
		Limits of Si MOSFETs and Their Application Dependencies", Proc. IEEE, vol. 89, no. 3, pp. 259-288,	
		2001.	
	7	Semiconductor Industry Association, "International Technology Roadmap for Semiconductors	
		2002 Update", 2002.	
	8	Y. ZHANG, J. WANG, L. WANG, and B.-Y. NGUYEN, "Design of 10-nm-Scale Recessed Asymmetric Schottky	
		Barrier MOSFETs", IEEE Electron Device Letters, vol. 23, no. 7, pp. 419-421, 2002.	

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